

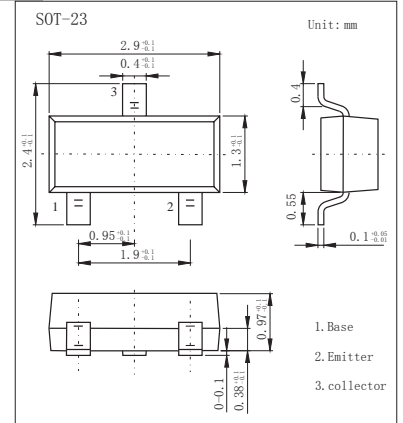
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Suitable for AF-Driver stages and low power output stages
- Complement to BC818
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-0.8	A
P_C	Collector Power Dissipation	300	mW
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-65-150	°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -25V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	100		630	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -300mA$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-0.7	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1V, I_C = -300mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA, f = 50MHz$		100		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		12		pF

CLASSIFICATION OF h_{FE}

Rank	16	25	40
Range $h_{FE(1)}$	100-250	160-400	250-630
Marking	5E	5F	5G